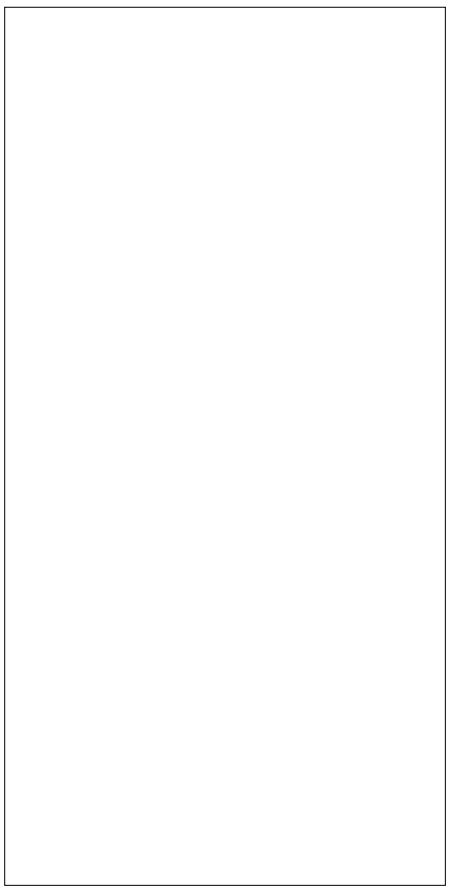
w -19.-0. 8 J 3 Tw A. (E)CJ0-2131. (1(87 (C)0.4)Tj 64z>773-06Tc 0 Tw256 Tm -83(



Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	2.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33	- -	MAX.	25	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3k	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	35	mA
				55	
I_H	I_T =100mA		MAX.	30	mA
dV/dt	V_D=540V Gate Open T_j =125		MIN.	2500	V s
(dI/dt)c	(dV/dt)c=1 9 V j=1225		MIN.	8	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j=25		TYP.	3	s
t_{off}				30	
V_{CL}	I_{CL}=0.1mA t_p=1ms		MIN.	850	V

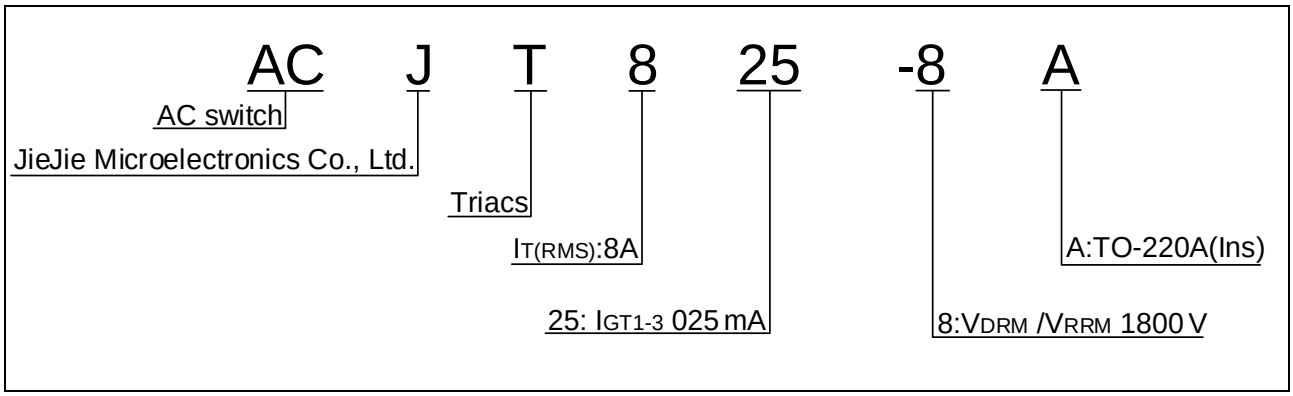
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX .)	Unit
V_{TM}	I_{TM} =10A t_p=380 s	T_j=25	1.4	V
V_{TO}	Threshold voltage	T_j=125	0.78	V
R_D	Dynamic resistance	T_j=125	38	P
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	5	A
I_{RRM}		T_j=125	0.5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.5	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

ORDERING INFORMATION



MARKING

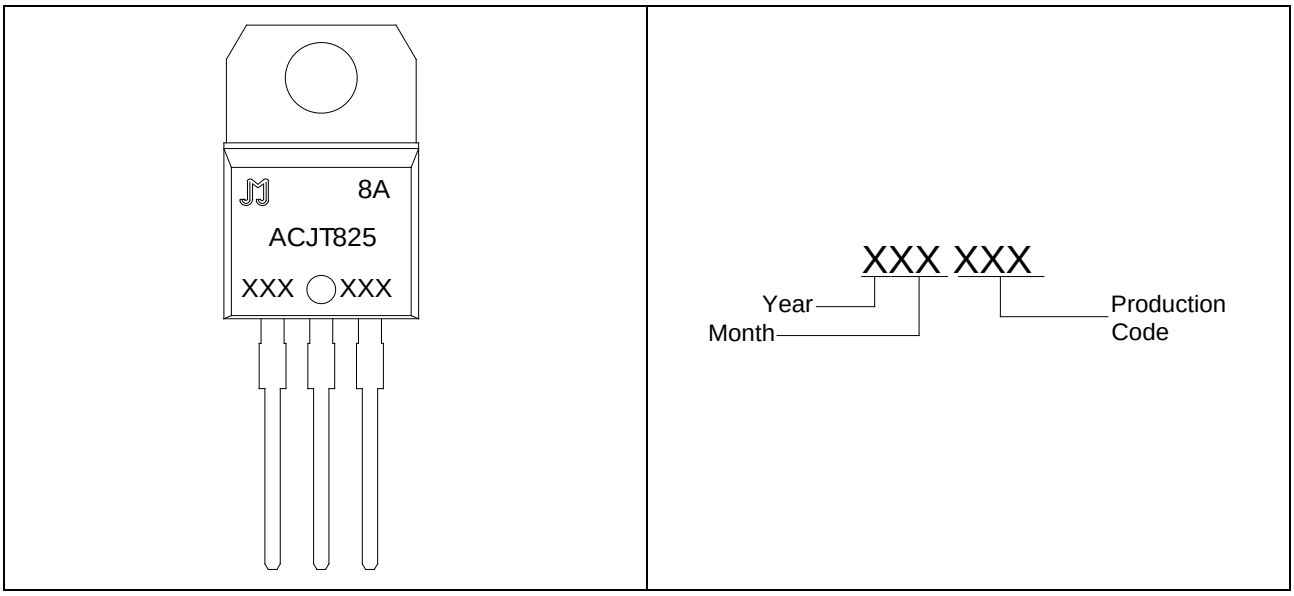
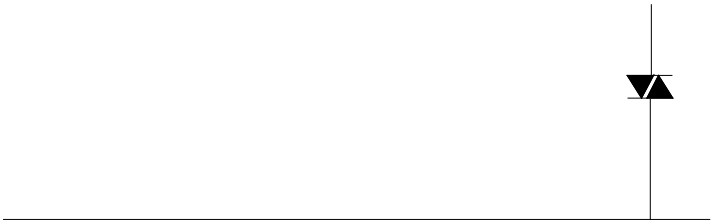


FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



ORDERING INFORMTON

Order coe	Voltage (5 ( )	]TJ 0 Tc 0 Tw 4.	Package	Base qty. (p	Delivery mode	0.498 scn
ACJT825-8A	800	25	TO-220A(In	50	Tube	

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last updated
Oct.13, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA